

#112 Andl.
M. Baunson
PATENT
81754.0064 9/7/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
Toshihiko HIGUCHI
Serial No: 09/910,447
Filed: July 19, 2001
For: SEMICONDUCTOR DEVICE
HAVING A CONTROLLED GATE
SHAPE AND METHOD FOR
MANUFACTURING THE SAME
(Amended)

Art Unit: 2814
Examiner: Thao X. Le

I hereby certify that this correspondence
is being transmitted via facsimile to
(703) 872-9318: Commissioner for
Patents, Washington D.C. 20231, on

September 5, 2002

Date of Deposit

Diane Zynn

Name

Signature

09/08/02

Date

FAX COPY RECEIVED

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

SEP 5 2002

TECHNOLOGY CENTER 2800

Dear Sir:

In response to the Office Action dated June 5, 2002, please amend the above-referenced application as follows:

IN THE TITLE:

Please amend the title to read "Semiconductor Device Having a Controlled Gate Shape and Method for Manufacturing the Same"

IN THE CLAIMS:

Please cancel claim 8 without prejudice.

Please replace the text of claims 1, 5 and 9-12 with the following text:

1. A semiconductor device comprising:
a semiconductor substrate;
a gate electrode formed on the semiconductor substrate through a gate dielectric layer;

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01 FC:102
02 FC:103

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